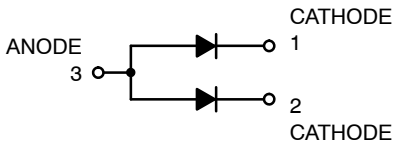
Dual Switching Diode Common Anode

BAW56M3T5G

70 V
DUAL COMMON ANODE
SWITCHING DIODE

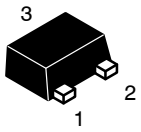
The BAW56M3T5G device is a spin−off of our popular SOT−23 three−leaded device. It is designed for switching applications and is housed in the SOT−723 surface mount package. This device is ideal for low−power surface mount applications where board space is at a premium.



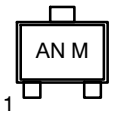
Features

- Reduces Board Space
- This is a Halide−Free Device
- This is a Pb−Free Device

MARKING DIAGRAM



SOT−723
CASE 631AA
STYLE 4



AN = Specific Device Code
M = Date Code

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	75	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	 265 2.1	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	640 5.1	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

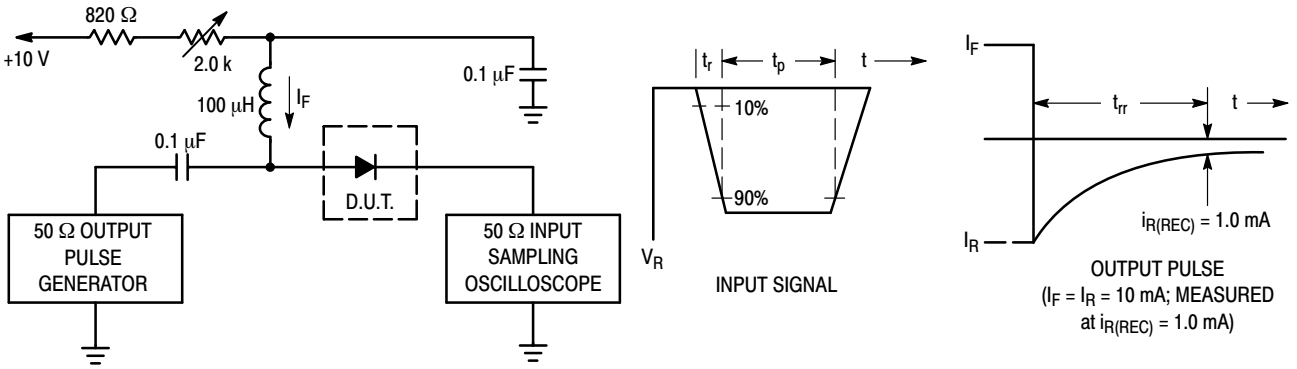
ORDERING INFORMATION

Device	Package	Shipping†
BAW56M3T5G	SOT−723 (Pb−Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Each Diode)

Characteristic		Symbol	Min	Max	Unit
Reverse Breakdown Voltage	($I_{(BR)}$ = 100 μA)	$V_{(BR)}$	70	–	V
Reverse Voltage Leakage Current		I_R			μA
	(V_R = 25 V, T_J = 150°C)		–	30	
	(V_R = 70 V)		–	2.5	
	(V_R = 70 V, T_J = 150°C)		–	50	
Diode Capacitance	(V_R = 0 V, f = 1.0 MHz)	C_D	–	2.0	pF
Forward Voltage		V_F			mV
	(I_F = 1.0 mA)		–	715	
	(I_F = 10 mA)		–	855	
	(I_F = 50 mA)		–	1000	
	(I_F = 150 mA)		–	1250	
Reverse Recovery Time (I_F = I_R = 10 mA, $I_{R(REC)}$ = 1.0 mA) (Figure 1)	R_L = 100 Ω	t_{rr}	–	6.0	ns



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

Curves Applicable to Each Cathode

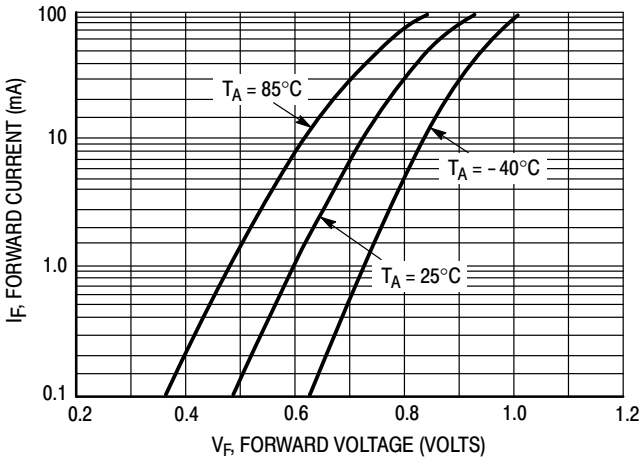


Figure 2. Forward Voltage

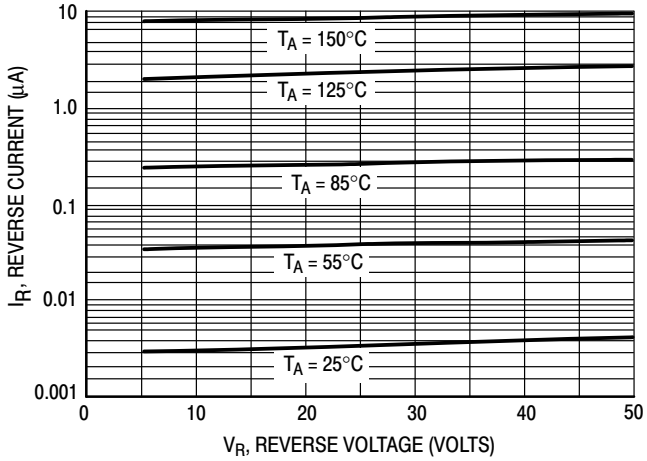


Figure 3. Leakage Current

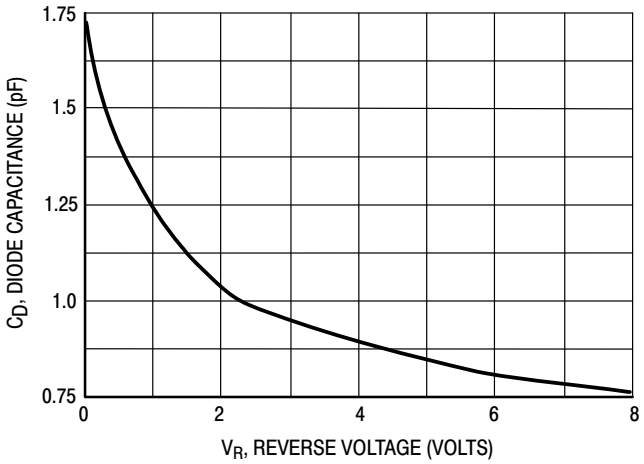
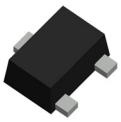


Figure 4. Capacitance

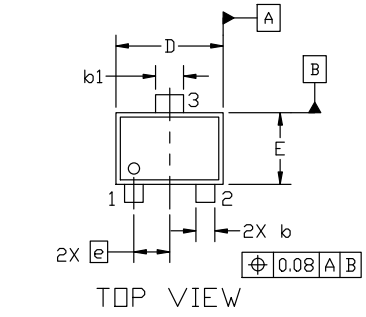


SOT−723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

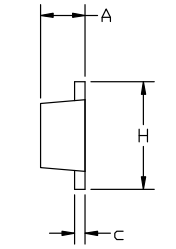
DATE 24 JAN 2024

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

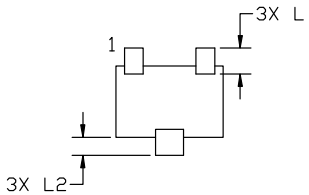
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



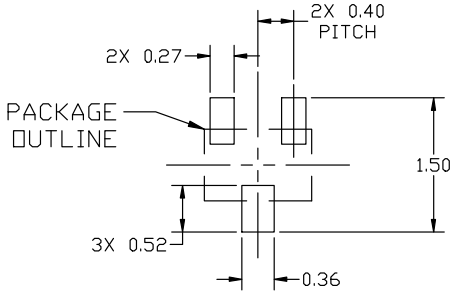
TOP VIEW



SIDE VIEW



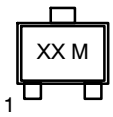
BOTTOM VIEW



RECOMMENDED MOUNTING
FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

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DESCRIPTION:	**SOT−723 1.20x0.80x0.50, 0.40P**	**PAGE 1 OF 1**

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